

04 June 2003

## Updated Search (Th)

09/16/14, 407

L Number	Hits	Search Text	DB	Time stamp
	83427	204/\$.ccls. or 205/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 15:47
	224	(204/\$.ccls. or 205/\$.ccls.) and ((prevention or prevent or preventing or prevented or inhibit or inhibition or inhibiting or inhibited or prohibit or prohibited or prohibiting) near (etch or etched or etching))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 14:19
	2	(204/\$.ccls. or 205/\$.ccls.) and (((prevention or prevent or preventing or prevented or inhibit or inhibition or inhibiting or inhibited or prohibit or prohibited or prohibiting) near (etch or etched or etching)) with seed)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 14:23
	13	(204/\$.ccls. or 205/\$.ccls.) and (((prevention or prevent or preventing or prevented or inhibit or inhibition or inhibiting or inhibited or prohibit or prohibited or prohibiting) near (etch or etched or etching)) with (potential or voltage or current))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 14:25
	695	(204/\$.ccls. or 205/\$.ccls.) and (cathodic adj protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 14:26
	50	((204/\$.ccls. or 205/\$.ccls.) and (cathodic adj protection)) and (semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 14:28
	771	(204/\$.ccls. or 205/\$.ccls.) and (((cathode or substrate or wafer or semiconductor) near (immers\$3 or submer\$4 or lower\$3)) with (potential or voltage or current))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 15:53
	10	(204/\$.ccls. or 205/\$.ccls.) and (((cathode or substrate or wafer or semiconductor) near (immers\$3 or submer\$4 or lower\$3)) with (potential or voltage or current) with seed)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 14:55
	2	6432821.bn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 15:08
	3	("6245676"   "6297157"   "6340633"   "2002/0004301"   "2002/0022363").PN.	USPAT	2003/06/02 14:56
	4	us-20020004301-\$ did. or us-20020022363-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 15:13
	4	4461680.bn. 6261433.bn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 15:20
	1	1999-582816.NRAN.	DERWENT	2003/06/02 15:18

	5	2882209.pn. 2742413.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 15:20
	462	205/\$.ccls. and (((cathode or substrate or wafer or semiconductor) near (immers\$3 or submer\$4 or lower\$3)) with (potential or voltage or current))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 16:17
	2	6334419.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 15:54
	79	(205/\$.ccls. and (((cathode or substrate or wafer or semiconductor) near (immers\$3 or submer\$4 or lower\$3)) with (potential or voltage or current))) and (pulse or pulsing or pulsed)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 16:17
	467	205/\$.ccls. and (((cathode or substrate or wafer or semiconductor) near (immers\$3 or submer\$4 or lower\$3)) with (potential or voltage or current or bias or biased or biasing))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 16:17
	.83	(205/\$.ccls. and (((cathode or substrate or wafer or semiconductor) near (immers\$3 or submer\$4 or lower\$3)) with (potential or voltage or current or bias or biased or biasing))) and (pulse or pulsing or pulsed)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 16:41
	5	205/\$.ccls. and ((immersion or entry) adj (voltage or bias or potential))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/02 16:49
	2	6162344.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 10:02
	72	205/105.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 12:06
	22	(US-6551484-\$ or US-6074544-\$ or US-6432821-\$ or US-6340633-\$ or US-6245676-\$ or US-6261433-\$ or US-6440291-\$ or US-6406611-\$ or US-5595638-\$ or US-5348640-\$ or US-4537663-\$ or US-6197179-\$ or US-6162344-\$ or US-6409903-\$).did. or (US-20030034250-\$ or US-20020084189-\$ or US-20020074234-\$ or US-20020022363-\$ or US-20010015321-\$ or US-20020112964-\$ or US-20020011415-\$).did. or (WO-9954527-\$).did.	USPAT; US-PGPUB; EPO	2003/06/03 11:13

	1	((US-6551484-\$ or US-6074544-\$ or US-6432821-\$ or US-6340633-\$ or US-6245676-\$ or US-6261433-\$ or US-6440291-\$ or US-6406611-\$ or US-5595638-\$ or US-5348640-\$ or US-4537663-\$ or US-6197179-\$ or US-6162344-\$ or US-6409903-\$).did. or (US-20030034250-\$ or US-20020084189-\$ or US-20020074234-\$ or US-20020022363-\$ or US-20010015321-\$ or US-20020112964-\$ or US-20020011415-\$).did. or (WO-9954527-\$).did.) and strike 205/\$.ccls. and (pulse or pulsed or pulsing) and seed	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 11:14
	148	205/\$.ccls. and ((high near (potential or voltage or current)) with (strike or nucleation))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 14:17
	32	(204/\$.ccls. or 205/\$.ccls.) and (unitary or unified) and (electroless with electroplating)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 14:19
	27	(204/\$.ccls. or 205/\$.ccls.) and (unitary or unified) and (electroless with electroplating) and seed	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 15:50
	6	(204/\$.ccls. or 205/\$.ccls.) and (unitary or unified) and (electroless with electroplating) and seed	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 15:49
	47	(204/\$.ccls. or 205/\$.ccls.) and system and (robot or robotic) and (electroless with electroplating) and seed	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 15:56
	12	(204/\$.ccls. or 205/\$.ccls.) and system and (robot or robotic) and (electroless with electroplating) and seed and (pulse or pulsed or pulsing)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 16:05
	2	6277263.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/03 16:47